

# RGTH00TS65

### 650V 50A Field Stop Trench IGBT

V <sub>CES</sub>	650V
I <sub>C(100°C)</sub>	50A
V <sub>CE(sat) (Typ.)</sub>	1.6V
$P_D$	277W

## ● Features

- 1) Low Collector Emitter Saturation Voltage
- 2) High Speed Switching
- 3) Low Switching Loss & Soft Switching
- 4) Pb free Lead Plating; RoHS Compliant

### Applications

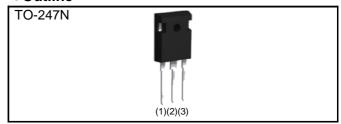
**PFC** 

**UPS** 

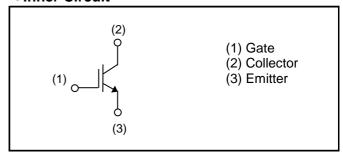
**Power Conditioner** 

ΙH

#### Outline



### ●Inner Circuit



Packaging Specifications

<del> </del>	
Packaging	Tube
Reel Size (mm)	-
Tape Width (mm)	-
Basic Ordering Unit (pcs)	450
Taping Code	C11
Marking	RGTH00TS65
	Reel Size (mm)  Tape Width (mm)  Basic Ordering Unit (pcs)  Taping Code

### ● Absolute Maximum Ratings (at T<sub>C</sub> = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V <sub>CES</sub>	650	V
Gate - Emitter Voltage		$V_{GES}$	±30	V
Collector Current	T <sub>C</sub> = 25°C	I <sub>C</sub>	85	А
	T <sub>C</sub> = 100°C	<sub>c</sub> = 100°C		А
Pulsed Collector Current		I <sub>CP</sub> *1	200	А
Power Dissipation	T <sub>C</sub> = 25°C	P <sub>D</sub>	277	W
	T <sub>C</sub> = 100°C	P <sub>D</sub>	138	W
Operating Junction Temperature		T <sub>j</sub>	-40 to +175	°C
Storage Temperature		T <sub>stg</sub>	-55 to +175	°C

<sup>\*1</sup> Pulse width limited by T<sub>jmax.</sub>

### ●Thermal Resistance

Darameter	Symbol	Values			Unit
Parameter		Min.	Тур.	Max.	Offic
Thermal Resistance IGBT Junction - Case	$R_{\theta(j-c)}$	-	-	0.54	°C/W

## ●IGBT Electrical Characteristics (at T<sub>j</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Тур.	Max.	Unit
Collector - Emitter Breakdown Voltage	BV <sub>CES</sub>	$I_C = 10 \mu A, V_{GE} = 0 V$	650	1	ı	V
Collector Cut - off Current	I <sub>CES</sub>	$V_{CE} = 650V, V_{GE} = 0V$	1	1	10	μΑ
Gate - Emitter Leakage Current	I <sub>GES</sub>	$V_{GE} = \pm 30V, V_{CE} = 0V$	-	-	±200	nA
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	$V_{CE} = 5V, I_{C} = 34.7 \text{mA}$	4.5	5.5	6.5	V
Collector - Emitter Saturation Voltage	V <sub>CE(sat)</sub>	$I_C = 50A$ , $V_{GE} = 15V$ $T_j = 25$ °C $T_j = 175$ °C	-	1.6 2.1	2.1	V

## ●IGBT Electrical Characteristics (at T<sub>j</sub> = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Limit
			Min.	Тур.	Max.	Unit
Input Capacitance	C <sub>ies</sub>	V <sub>CE</sub> = 30V	-	2740	-	
Output Capacitance	C <sub>oes</sub>	$V_{GE} = 0V$	-	106	-	pF
Reverse Transfer Capacitance	C <sub>res</sub>	f = 1MHz	-	43	-	
Total Gate Charge	$Q_g$	V <sub>CE</sub> = 300V	-	94	-	
Gate - Emitter Charge	$Q_ge$	I <sub>C</sub> = 50A	-	22	-	nC
Gate - Collector Charge	$Q_{gc}$	V <sub>GE</sub> = 15V	-	31	-	
Turn - on Delay Time	t <sub>d(on)</sub>	$I_C = 50A, V_{CC} = 400V$	-	39	-	
Rise Time	t <sub>r</sub>	$V_{GE} = 15V, R_G = 10\Omega$	-	63	-	
Turn - off Delay Time	t <sub>d(off)</sub>	T <sub>j</sub> = 25°C	-	143	-	ns
Fall Time	t <sub>f</sub>	Inductive Load	-	50	-	
Turn - on Delay Time	t <sub>d(on)</sub>	$I_C = 50A, V_{CC} = 400V$	-	39	-	
Rise Time	t <sub>r</sub>	$V_{GE} = 15V, R_G = 10\Omega$	-	63	-	
Turn - off Delay Time	t <sub>d(off)</sub>	T <sub>j</sub> = 175°C	-	159	-	ns
Fall Time	t <sub>f</sub>	Inductive Load	-	62	-	
		I <sub>C</sub> = 200A, V <sub>CC</sub> = 520V				
Reverse Bias Safe Operating Area	RBSOA	$V_P = 650V, V_{GE} = 15V$	FULL SQUARE			-
		$R_G = 60\Omega, T_j = 175^{\circ}C$				

Fig.1 Power Dissipation vs. Case Temperature

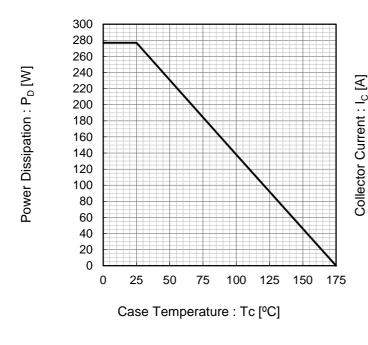
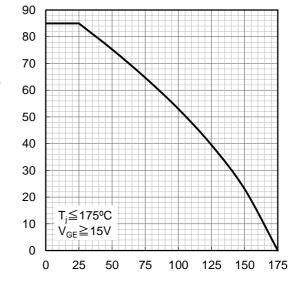
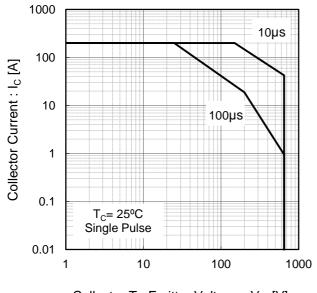


Fig.2 Collector Current vs. Case Temperature



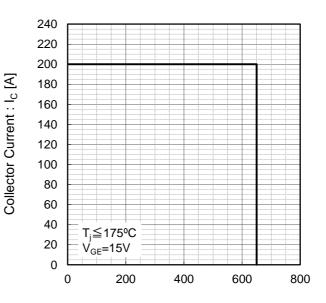
Case Temperature : Tc [°C]

Fig.3 Forward Bias Safe Operating Area



Collector To Emitter Voltage :  $V_{CE}[V]$ 

Fig.4 Reverse Bias Safe Operating Area



Collector To Emitter Voltage : V<sub>CE</sub>[V]

Fig.5 Typical Output Characteristics

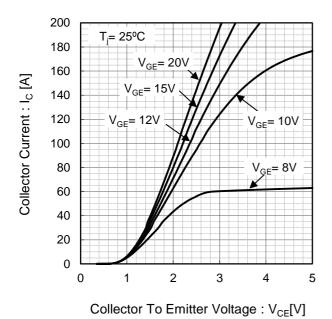
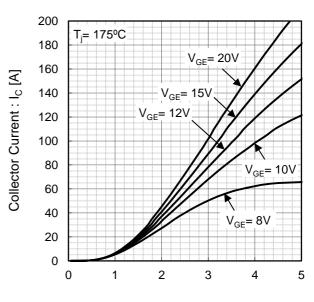


Fig.6 Typical Output Characteristics



Collector To Emitter Voltage : V<sub>CE</sub>[V]

Fig.7 Typical Transfer Characteristics

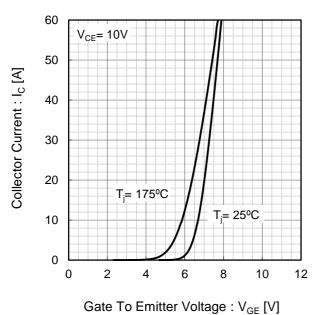
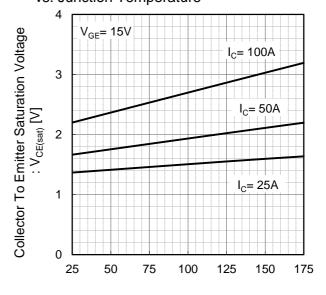


Fig.8 Typical Collector To Emitter Saturation Voltage vs. Junction Temperature



Junction Temperature : T<sub>i</sub> [°C]

Fig.9 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage

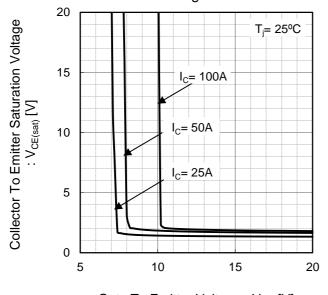
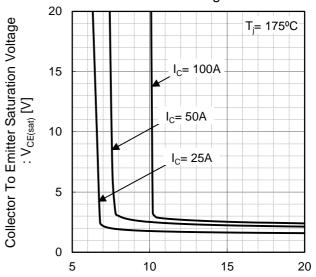


Fig.10 Typical Collector To Emitter Saturation Voltage vs. Gate To Emitter Voltage



Gate To Emitter Voltage : V<sub>GE</sub> [V]

Gate To Emitter Voltage : V<sub>GE</sub> [V]

vs. Collector Current  $t_{d(off)}$   $t_{d(on)}$   $t_{d(on)}$   $V_{CC}=400V, V_{GE}=15V$   $R_{G}=10\Omega, T_{j}=175^{\circ}C$ Inductive load

30

20

10

Fig.11 Typical Switching Time

Collector Current : I<sub>C</sub> [A]

40 50 60 70 80 90 100

Fig.12 Typical Switching Time
vs. Gate Resistance

1000

t<sub>d</sub>

Gate Resistance :  $R_G[\Omega]$ 

Fig.13 Typical Switching Energy Losses vs. Collector Current 10 Switching Energy Losses [mJ] 1  $\mathsf{E}_{\mathsf{off}}$ 0.1  $V_{CC}$ =400V,  $V_{GE}$ =15V  $R_{G}$ =10 $\Omega$ ,  $T_{j}$ =175°C Inductive load 0.01 10 20 30 40 50 60 70 80 90 100 Collector Current : I<sub>C</sub> [A]

vs. Gate Resistance 10 Switching Energy Losses [mJ]  $E_{off}$ 1  $E_{on}$ 0.1  $V_{CC}$ =400V,  $I_{C}$ =50A  $V_{GE}$ =15V,  $T_{j}$ =175°C Inductive load 0.01 0 10 20 30 40 50 Gate Resistance :  $R_G[\Omega]$ 

Fig.14 Typical Switching Energy Losses

Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] Coes 100 Cres 10 f=1MHz  $V_{GE}=0V$ T;=25°C 0.01 0.1 1 10 100 Collector To Emitter Voltage : V<sub>CE</sub>[V]

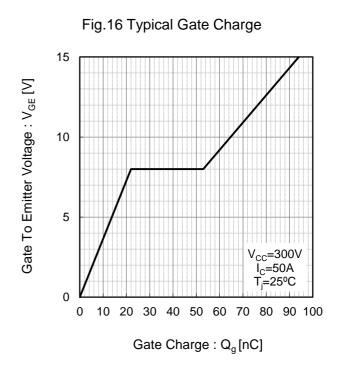
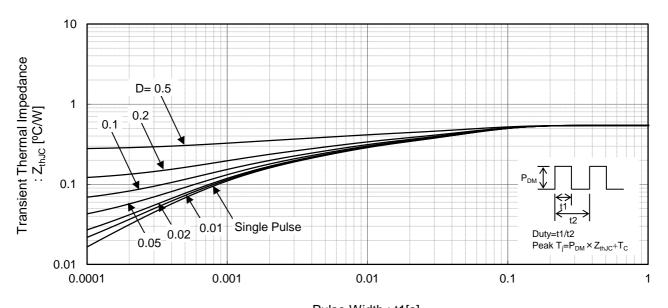


Fig.17 IGBT Transient Thermal Impedance



Pulse Width: t1[s]

### •Inductive Load Switching Circuit and Waveform

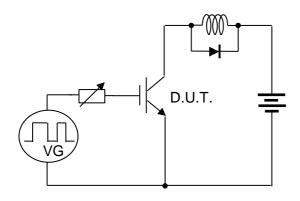


Fig.18 Inductive Load Circuit

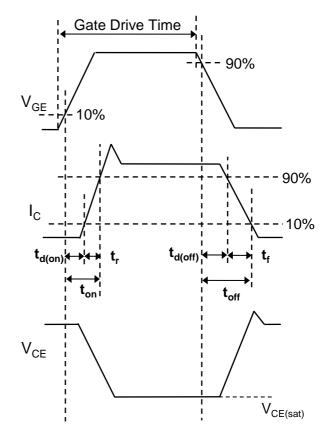


Fig.19 Inductive Load Waveform

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